



Attorney's Docket No. 5308-156

Image 2811
9
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.
Serial No.: 09/911,995
Filed: July 24, 2001

Group Art Unit: 2811
Confirmation No.: 5240
Examiner: Gene M. Munson

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND
METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A
SHORTING CHANNEL

Date: February 04, 2004

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

The Commissioner is authorized to charge \$180.00 for the fee specified in 37 C.F.R. § 1.17(p) and any additional fee or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek
Registration No. 48,568

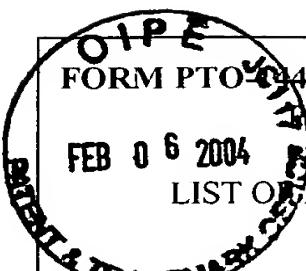
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U.S. Department of Commerce
Patent and Trademark Office
LIST OF DOCUMENTS CITED BY APPLICANT
(Use several sheets if necessary)

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U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1	Williams et al., "Passivation of the 4-H SiC/SiO ₂ Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.
	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.

EXAMINER

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DATE CONSIDERED

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.